

650V-40A Trench and Field Stop IGBT

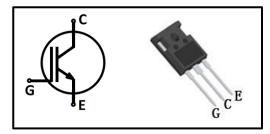
Features

- Easy parallel switching capability due to positive temperature coefficient in V_{CEsat}
- Low V_{CEsat}, fast switching
- High ruggedness, good thermal stability
- Very tight parameter distribution

Туре	Marking	Package Code
MPGW40N65E	MPG40N65E	TO-247-3

Applications

- UPS
- PFC
- **PTC Heater**
- **■** Climate Compressor



Maximum Rated Values 1

Parameter	Symbol	Value	Unit		
Collector-emitter voltage	V _{CE}	650	V		
DC collector current ²					
T _C =25°C		80] ,		
T _C =100°C] ['] C	40	Α		
Pulsed collector current ³	I _{Cpuls}	160			
Gate-emitter voltage	V	±20	\ \		
Transient Gate-emitter voltage (t _p ≤10us)	V_{GE}	±30	V		
Power dissipation					
T _C =25°C	D	250	w		
T _C =100°C	P _{tot}	125			
Operating junction temperature	T _j	-55~175	°C		
Storage temperature	T _{stg}	-55~150			

^{1:}Reference standard: JESD-022 2: limited by Tjmax 3: Tp limited by Tjmax ;



Thermal Characteristics

Parameter	Symbol	Min	Тур	Max	Unit
IGBT thermal resistance, junction-case	R _{thJC}	-	-	0.6	K/W
Thermal Resistance, junction-ambient	R _{thJA}	ı	1	40	r\/vv

Electrical Characteristics (at Tj=25°C, unless otherwise specified) Static Characteristics

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-emitter breakdown voltage	V _{(BR)CES}	V _{GE} =0V, I _C =0.25mA	650	-	-	
Collector-emitter saturation voltage	$V_{CE(sat)}$	V _{GE} =15V, I _C =40A T _j =25°C	1	1.50		
		T _j =125°C	ı	1.70	1	V
		T _j =150°C	-	1.80	-	
G-E threshold voltage	$V_{GE(th)}$	$I_C=0.8$ mA, $V_{CE}=V_{GE}$		5.5		
C-E leakage current	I _{CES}	V_{CE} =650V, V_{GE} =0V T_{j} =25°C	ı	ı	0.1	mA
		T _j =150°C	ı	ı	1	
G-E leakage current	I _{GES}	V _{CE} =0V, V _{GE} =20V	-	-	250	nA
Transconductance	g _{FS}	V _{CE} =20V, I _C =40A	-	-	-	S

Dynamic Characteristics

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Input capacitance	C _{iss}	V _{CE} =25V, V _{GE} =0V, f=1MHz	1	2700	1	
Output capacitance	C _{oss}		-	150	-	рF
Reverse transfer capacitance	C _{rss}		1	40	1	•
Gate charge	Q_{G}	V _{CC} =100V, I _C =40A, V _{GE} =15V	-	110	-	nC

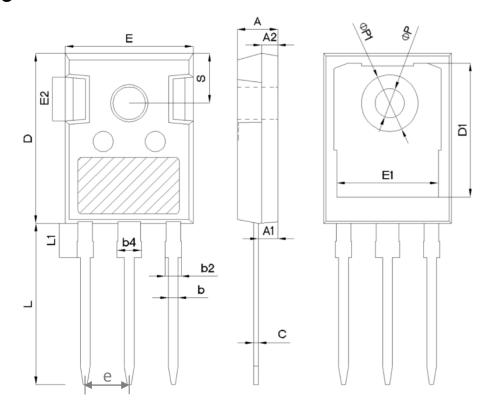


IGBT Switching Characteristics

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Turn-on delay time	t _{d(on)}	T 05°C	-	85	-	
Rise time	t _r	T _j =25°C, V _{CC} =400V,	-	55	-	
Turn-off delay time	t _{d(off)}	I _C =40A,	-	190	-	ns
Fall time	t _f	$V_{GE}=0/15V$, $R_{G}=10\Omega$,	-	40	-	
Turn-on energy	E _{on}	Inductive load	-	0.94	-	
Turn-off energy	E _{off}	(Test with	-	0.85	-	mJ
Total switching energy	E _{ts}	MPBW40N65E)	-	1.79	-	
Turn-on delay time	t _{d(on)}	T_150°C	-	85	-	
Rise time	t _r	- T _j =150°C, V _{CC} =400V,	-	70	-	
Turn-off delay time	t _{d(off)}	I _C =40A,	-	210	-	ns
Fall time	t _f	V_{GE} =0/15V, R_{G} =10 Ω , Inductive load (Test with MPBW40N65E)	-	80	-	
Turn-on energy	E _{on}		-	1.94	-	
Turn-off energy	E _{off}		-	1.12	-	mJ
Total switching energy	E _{ts}		-	3.06	-	



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		mm	
SYMBOL	MIN	NOM	MAX
A	4.80	5.00	5.20
A1	2.21	2.41	2.61
A2	1.85	2.00	2.15
b	1.11	1.21	1.36
b2	1.91	2.01	2.21
b4	2.91	3.01	3.21
c	0.51	0.61	0.75
D	20.70	21.00	21.30
D1	16.25	16.55	16.85
Е	15.50	15.80	16.10
E1	13.00	13.30	13.60
E2	4.80	5.00	5.20
E3	2.30	2.50	2.70
e		5.44BSC	
L	19.62	19.92	20.22
L1	-	-	4.30
ФР	3.40	3.60	3.80
ФР1	-	-	7.30
S		6.15BSC	



Revision History:

Revision	Date	Subjects (major changes since last revision)
1.0	2022-09	Initial Version



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